

Specification Sheet

Gallium Arsenide Wafer

(GaAs, Dia: 150 ± 0.5 mm, P Type)

Stock No: NS6130-10-1494, CAS: 1303-00-0

Product	:	Gallium Arsenide Wafer
Stock No	:	NS6130-10-1494
CAS	:	1303-00-0
Diameter	:	150 ± 0.5 mm
Thickness	:	450 μ m
Dopant	:	Zn
Orientation	:	(100) 2° to (110) $\pm 0.1^\circ$, alpha = 45 $^\circ$
Growth Method	:	VGF (Vertical Gradient Freeze)
Surface	:	One Side Polished
Resistivity (ohm.cm) Seed End	:	5.87E-03
Hall mobility (cm ² V ⁻¹ s ⁻¹) Seed	:	72
End		
Carrier concentration (cm ⁻³) Seed	:	1.48E+19
End		
Average EPD (cm ⁻²) Seed End	:	891
Resistivity (ohm.cm) Tail End	:	2.97E-03
Hall mobility (cm ² V ⁻¹ s ⁻¹) Tail	:	55
End		
Carrier concentration (cm ⁻³) Tail	:	3.83E+19
End		
Average EPD (cm ⁻²) Tail End	:	1108
Main Inspect Verifier	:	Manager QC

Note: Product Specification are subject to amendment and may change over time

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